Amendments to the Specification:

Please replace the paragraph beginning on page 2, line 18, with the following rewritten paragraph:

Therefore, in order to avert the aforementioned situation, the substrate is subjected to a processing in such a manner that by spin-coating the resist thereon to form the resist film on the substrate, and thereafter the resist film on the peripheral edge of the substrate is previously removed. In the processing, a chemical liquid by which the resist is dissolved is fed to the resist on the peripheral edge of the substrate while rotating the substrate horizontally around a specified rotation center, and the resist film on the peripheral edge of the substrate is thereby dissolved and removed.

Please replace the paragraph beginning on page 3, line 2, with the following rewritten paragraph:

For example, a technique to remove the unnecessary resist film on the peripheral edge of the substrate includes a method disclosed in Patent Document 1-Japanese Patent

Application No. 2001-259502.

Please cancel the paragraph at page 3, lines 23-24.

Please replace the paragraph beginning on page 4, line 1, with the following rewritten paragraph:

Out of the aforementioned photo mask blank, a transfer mask (in some cases, described as a reticle hereunder) mounted on an exposure device (in some cases, described as a stepper hereunder) for pattern transfer and used as a mask for a reduction exposure device during manufacturing a semiconductor integrated circuit, has a pattern composed of a light

shielding film containing chrome or the like formed by sputtering or the like on a transparent glass substrate whose main surface at least is finished into a mirror face. Usually, the reticle is attached, with attached onto the main surface of the side, substrate on which the transfer pattern is formed. formed, is directed toward the substrate to be subjected to transfer. Then, when the reticle is attached, it is vacuum-chucked to the peripheral edge of the main surface of the substrate, so as to have a wide pattern area and so as not to allow to place the substrate to be deviated in the proper position when the stepper is in operation.